

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VCX16821FT

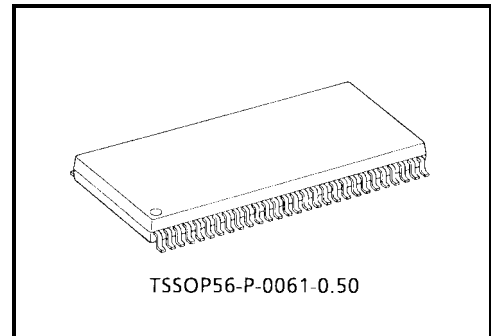
Low-Voltage 20-Bit D-Type Flip-Flop with 3.6-V Tolerant Inputs and Outputs

The TC74VCX16821FT is a high-performance CMOS 20-bit D-type flip-flop. Designed for use in 1.8-V, 2.5-V or 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

It is also designed with overvoltage tolerant inputs and outputs up to 3.6 V.

The device is byte controlled with each byte functioning identically, but independent of the other. Control pins can be shorted together to obtain full 20-bit operation. The following description applies to each byte. The twenty flip-flops will store the state of their individual D inputs that meet the setup and hold time requirements on the LOW-to-HIGH Clock (CK) transition. When the OE input is high, the outputs are in a high-impedance state. This device is designed to be used with 3-state memory address drivers, etc.

All inputs are equipped with protection circuits against static discharge.

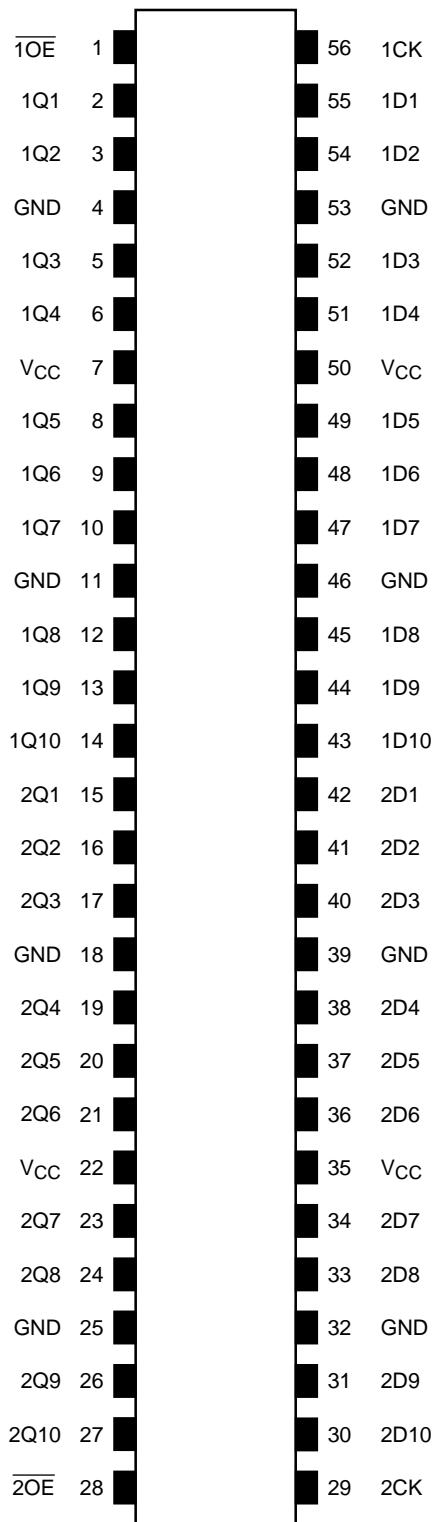


Weight: 0.25 g (typ.)

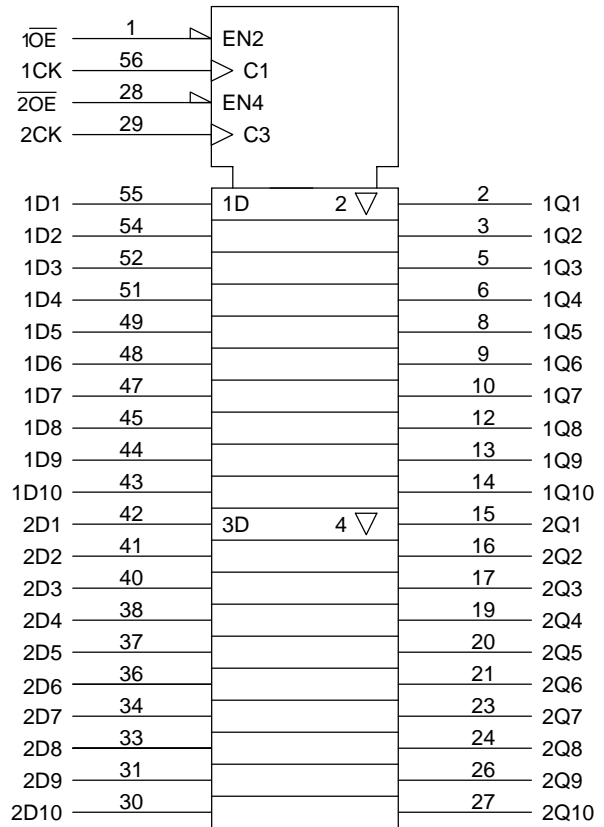
Features

- Low-voltage operation: $V_{CC} = 1.8$ to 3.6 V
- High-speed operation : $t_{pd} = 3.5$ ns (max) ($V_{CC} = 3.0$ to 3.6 V)
: $t_{pd} = 4.4$ ns (max) ($V_{CC} = 2.3$ to 2.7 V)
: $t_{pd} = 8.8$ ns (max) ($V_{CC} = 1.8$ V)
- Output current: $I_{OH}/I_{OL} = \pm 24$ mA (min) ($V_{CC} = 3.0$ V)
: $I_{OH}/I_{OL} = \pm 18$ mA (min) ($V_{CC} = 2.3$ V)
: $I_{OH}/I_{OL} = \pm 6$ mA (min) ($V_{CC} = 1.8$ V)
- Latch-up performance: ± 300 mA
- ESD performance: Machine model $> \pm 200$ V
: Human body model $> \pm 2000$ V
- Package: TSSOP (thin shrink small outline package)
- 3.6-V tolerant function and power-down protection provided on all inputs and outputs




Pin Assignment (top view)






IEC Logic Symbol



Truth Table

Inputs			Outputs
$\overline{1OE}$	1CK	1D1-1D10	1Q1-1Q10
H	X	X	Z
L		X	Qn
L		L	L
L		H	H

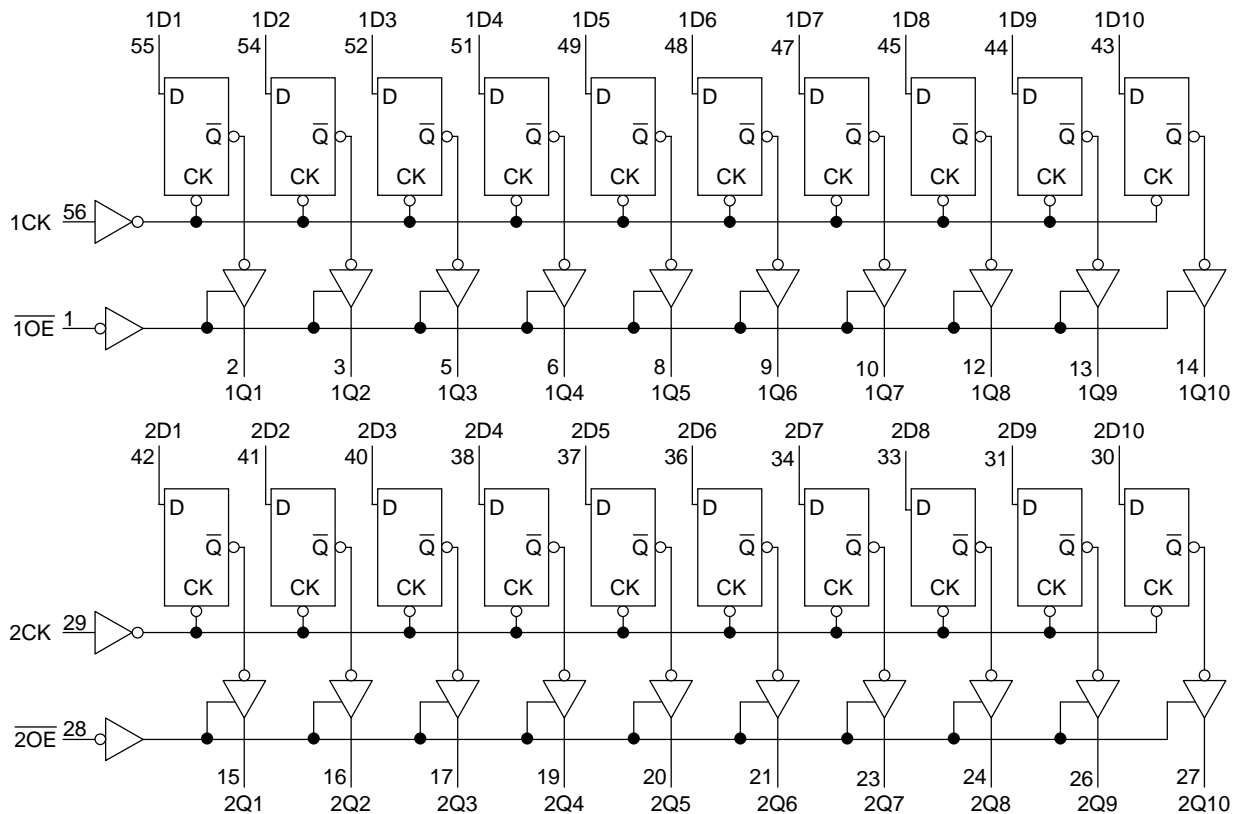
Inputs			Outputs
$\overline{2OE}$	2CK	2D1-2D10	2Q1-2Q10
H	X	X	Z
L		X	Qn
L		L	L
L		H	H

X: Don't care

Z: High impedance

Qn: No change

System Diagram



Maximum Ratings

Characteristics	Symbol	Rating	Unit
Power supply voltage	V_{CC}	-0.5 to 4.6	V
DC input voltage	V_{IN}	-0.5 to 4.6	V
DC output voltage	V_{OUT}	-0.5 to 4.6 (Note 1)	V
		-0.5 to $V_{CC} + 0.5$ (Note 2)	
Input diode current	I_{IK}	-50	mA
Output diode current	I_{OK}	± 50 (Note 3)	mA
DC output current	I_{OUT}	± 50	mA
Power dissipation	P_D	400	mW
DC V_{CC} /ground current per supply pin	I_{CC}/I_{GND}	± 100	mA
Storage temperature	T_{stg}	-65 to 150	$^{\circ}C$

Note 1: OFF state

Note 2: High or low state. I_{OUT} absolute maximum rating must be observed.

Note 3: $V_{OUT} < GND$, $V_{OUT} > V_{CC}$

Recommended Operating Range

Characteristics	Symbol	Rating	Unit
Power supply voltage	V_{CC}	1.8 to 3.6	V
		1.2 to 3.6 (Note 4)	
Input voltage	V_{IN}	-0.3 to 3.6	V
Output voltage	V_{OUT}	0 to 3.6 (Note 5)	V
		0 to V_{CC} (Note 6)	
Output current	I_{OH}/I_{OL}	± 24 (Note 7)	mA
		± 18 (Note 8)	
		± 6 (Note 9)	
Operating temperature	T_{opr}	-40 to 85	$^{\circ}C$
Input rise and fall time	dt/dv	0 to 10 (Note 10)	ns/V

Note 4: Data retention only

Note 5: OFF state

Note 6: High or low state

Note 7: $V_{CC} = 3.0$ to 3.6 V

Note 8: $V_{CC} = 2.3$ to 2.7 V

Note 9: $V_{CC} = 1.8$ V

Note 10: $V_{IN} = 0.8$ to 2.0 V, $V_{CC} = 3.0$ V

Electrical Characteristics

DC Characteristics (Ta = -40 to 85°C, 2.7 V < VCC ≤ 3.6 V)

Characteristics		Symbol	Test Condition		VCC (V)	Min	Max	Unit
Input voltage	H-level	V _{IH}	—		2.7 to 3.6	2.0	—	V
	L-level	V _{IL}	—		2.7 to 3.6	—	0.8	
Output voltage	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.7 to 3.6	V _{CC} - 0.2	—	V
				I _{OH} = -12 mA	2.7	2.2	—	
				I _{OH} = -18 mA	3.0	2.4	—	
				I _{OH} = -24 mA	3.0	2.2	—	
	L-level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.7 to 3.6	—	0.2	
				I _{OL} = 12 mA	2.7	—	0.4	
				I _{OL} = 18 mA	3.0	—	0.4	
				I _{OL} = 24 mA	3.0	—	0.55	
Input leakage current		I _{IN}	V _{IN} = 0 to 3.6 V		2.7 to 3.6	—	±5.0	μA
3-state output OFF state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0 to 3.6 V		2.7 to 3.6	—	±10.0	μA
Power-off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	—	10.0	μA
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND		2.7 to 3.6	—	20.0	μA
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.7 to 3.6	—	±20.0	
Increase in I _{CC} per input		ΔI _{CC}	V _{IH} = V _{CC} - 0.6 V		2.7 to 3.6	—	750	

DC Characteristics (Ta = -40 to 85°C, 2.3 V ≤ VCC ≤ 2.7 V)

Characteristics		Symbol	Test Condition		VCC (V)	Min	Max	Unit
Input voltage	H-level	V _{IH}	—		2.3 to 2.7	1.6	—	V
	L-level	V _{IL}	—		2.3 to 2.7	—	0.7	
Output voltage	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.3 to 2.7	V _{CC} - 0.2	—	V
				I _{OH} = -6 mA	2.3	2.0	—	
				I _{OH} = -12 mA	2.3	1.8	—	
				I _{OH} = -18 mA	2.3	1.7	—	
	L-level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.3 to 2.7	—	0.2	
				I _{OL} = 12 mA	2.3	—	0.4	
				I _{OL} = 18 mA	2.3	—	0.6	
				I _{OL} = 18 mA	2.3	—	0.6	
Input leakage current		I _{IN}	V _{IN} = 0 to 3.6 V		2.3 to 2.7	—	±5.0	μA
3-state output OFF state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0 to 3.6 V		2.3 to 2.7	—	±10.0	μA
Power-off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	—	10.0	μA
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND		2.3 to 2.7	—	20.0	μA
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.3 to 2.7	—	±20.0	

DC Characteristics (Ta = -40 to 85°C, 1.8 V ≤ VCC < 2.3 V)

Characteristics		Symbol	Test Condition		VCC (V)	Min	Max	Unit
Input voltage	H-level	V _{IH}	—		1.8 to 2.3	0.7 × V _{CC}	—	V
	L-level	V _{IL}	—		1.8 to 2.3	—	0.2 × V _{CC}	
Output voltage	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	—	V
				I _{OH} = -6 mA	1.8	1.4	—	
	L-level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	1.8	—	0.2	
				I _{OL} = 6 mA	1.8	—	0.3	
Input leakage current		I _{IN}	V _{IN} = 0 to 3.6 V		1.8	—	±5.0	μA
3-state output OFF state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0 to 3.6 V		1.8	—	±10.0	μA
Power-off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	—	10.0	μA
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND		1.8	—	20.0	μA
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		1.8	—	±20.0	

AC Characteristics (Ta = -40 to 85°C, input: tr = tf = 2.0 ns, CL = 30 pF, RL = 500 Ω)

Characteristics	Symbol	Test Condition	VCC (V)	Min	Max	Unit
Maximum clock frequency	f _{max}	Figure 1, Figure 2	1.8	100	—	MHz
			2.5 ± 0.2	200	—	
			3.3 ± 0.3	250	—	
Propagation delay time (CK-Q)	t _{pLH} t _{pHL}	Figure 1, Figure 2	1.8	1.5	8.8	ns
			2.5 ± 0.2	1.0	4.4	
			3.3 ± 0.3	0.8	3.5	
3-state output enable time	t _{pZL} t _{pZH}	Figure 1, Figure 3	1.8	1.5	9.8	ns
			2.5 ± 0.2	1.0	4.7	
			3.3 ± 0.3	0.8	3.7	
3-state output disable time	t _{pLZ} t _{pHZ}	Figure 1, Figure 3	1.8	1.5	7.6	ns
			2.5 ± 0.2	1.0	4.2	
			3.3 ± 0.3	0.8	3.7	
Minimum pulse width (CK)	t _W (H) t _W (L)	Figure 1, Figure 2	1.8	4.0	—	ns
			2.5 ± 0.2	1.5	—	
			3.3 ± 0.3	1.5	—	
Minimum setup time	t _s	Figure 1, Figure 2	1.8	2.5	—	ns
			2.5 ± 0.2	1.5	—	
			3.3 ± 0.3	1.5	—	
Minimum hold time	t _h	Figure 1, Figure 2	1.8	1.0	—	ns
			2.5 ± 0.2	1.0	—	
			3.3 ± 0.3	1.0	—	
Output to output skew	t _{osLH} t _{osHL}	(Note 11)	1.8	—	0.5	ns
			2.5 ± 0.2	—	0.5	
			3.3 ± 0.3	—	0.5	

For C_L = 50 pF, add approximately 300 ps to the AC maximum specification.

Note 11: Parameter guaranteed by design.

$$(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$$

Dynamic Switching Characteristics

(Ta = 25°C, input: tr = tf = 2.0 ns, CL = 30 pF, RL = 500 Ω)

Characteristics	Symbol	Test Condition	VCC (V)	Typ.	Unit
Quiet output maximum dynamic VOL	VOLP	VIH = 1.8 V, VIL = 0 V (Note 12)	1.8	0.25	V
		VIH = 2.5 V, VIL = 0 V (Note 12)	2.5	0.6	
		VIH = 3.3 V, VIL = 0 V (Note 12)	3.3	0.8	
Quiet output minimum dynamic VOL	VOLV	VIH = 1.8 V, VIL = 0 V (Note 12)	1.8	-0.25	V
		VIH = 2.5 V, VIL = 0 V (Note 12)	2.5	-0.6	
		VIH = 3.3 V, VIL = 0 V (Note 12)	3.3	-0.8	
Quiet output minimum dynamic VOH	VOHV	VIH = 1.8 V, VIL = 0 V (Note 12)	1.8	1.5	V
		VIH = 2.5 V, VIL = 0 V (Note 12)	2.5	1.9	
		VIH = 3.3 V, VIL = 0 V (Note 12)	3.3	2.20	

Note 12: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	VCC (V)	Typ.	Unit
Input capacitance	CIN	—	1.8, 2.5, 3.3	6	pF
Output capacitance	CO	—	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	CPD	fIN = 10 MHz (Note 13)	1.8, 2.5, 3.3	20	pF

Note 13: CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/20 \text{ (per bit)}$$

AC Test Circuit

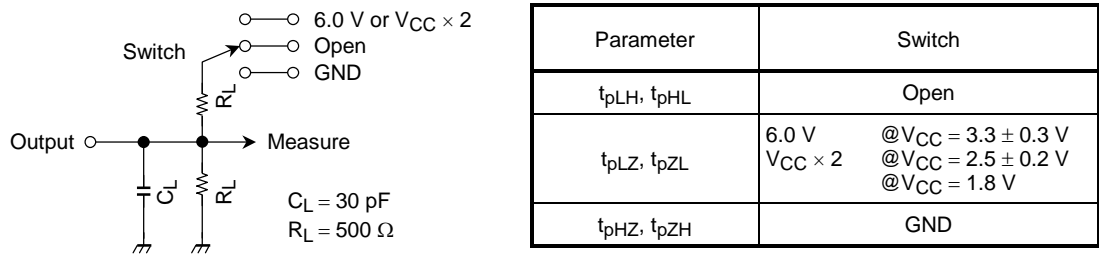


Figure 1

AC Waveform

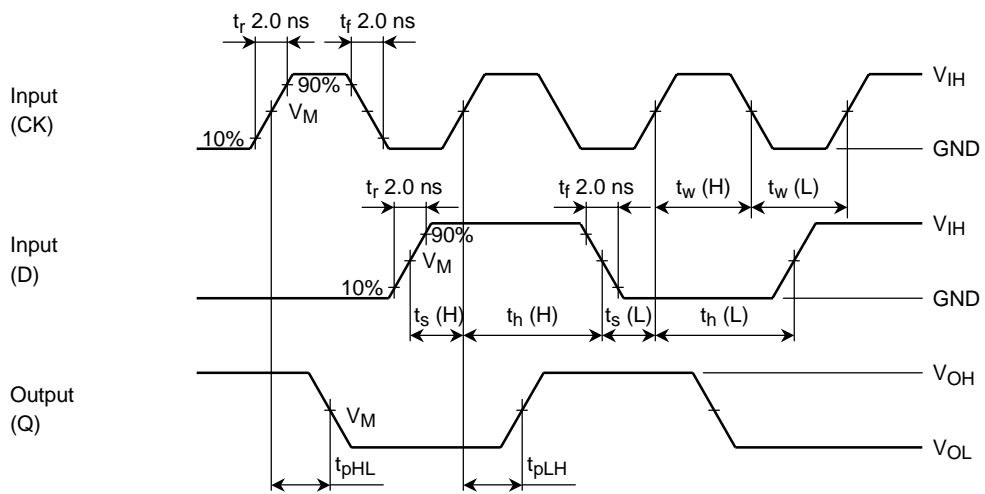


Figure 2 $t_{pLH}, t_{pHL}, t_w, t_s, t_h$

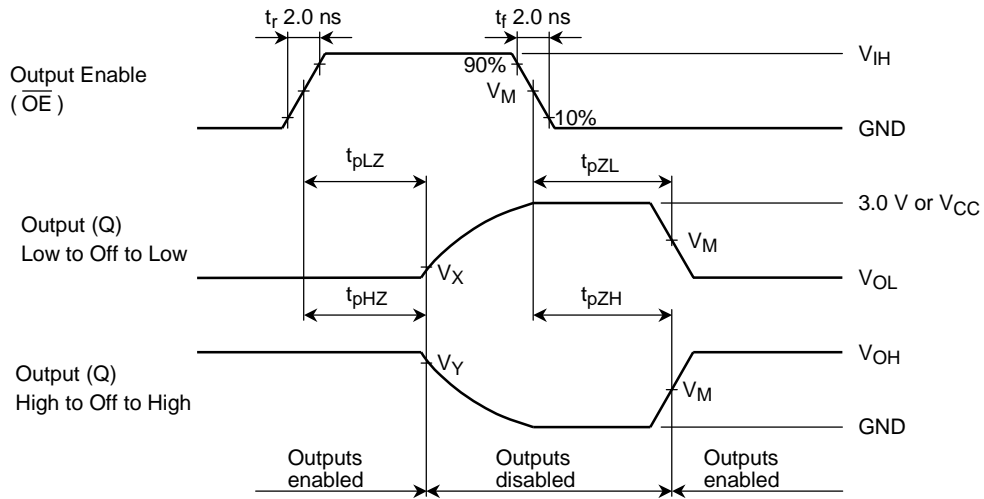


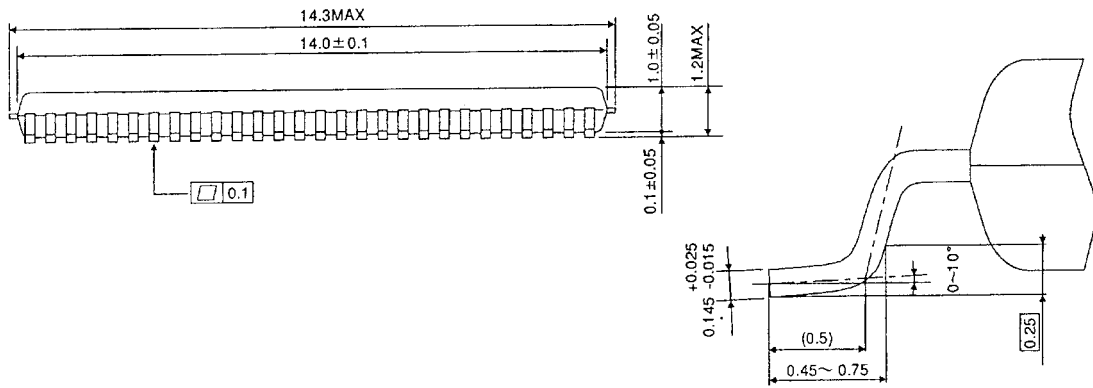
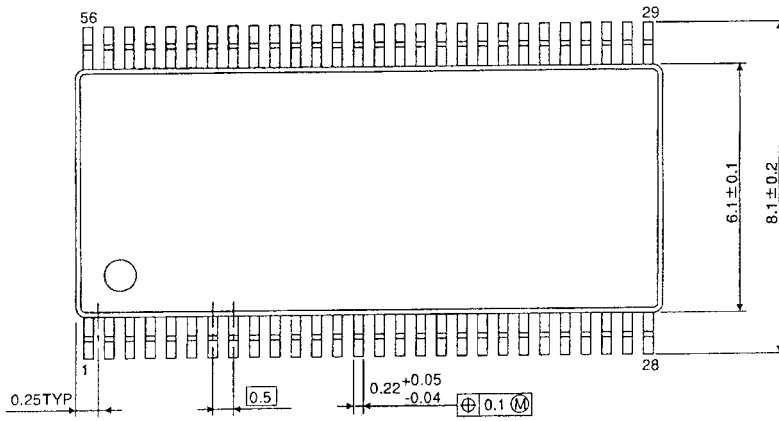
Figure 3 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

Symbol	V_{CC}		
	3.3 ± 0.3 V	2.5 ± 0.2 V	1.8 V
V_{IH}	2.7 V	V_{CC}	V_{CC}
V_M	1.5 V	$V_{CC}/2$	$V_{CC}/2$
V_X	$V_{OL} + 0.3$ V	$V_{OL} + 0.15$ V	$V_{OL} + 0.15$ V
V_Y	$V_{OH} - 0.3$ V	$V_{OH} - 0.15$ V	$V_{OH} - 0.15$ V

Package Dimensions

TSSOP56-P-0061-0.50

Unit : mm



Weight: 0.25 g (typ.)

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000707EBA

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